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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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ON Semiconductor®

FDMC035N10X1

N-Channel PowerTrench® MOSFET

100 V, 5.5 A, 37 mΩ

Features

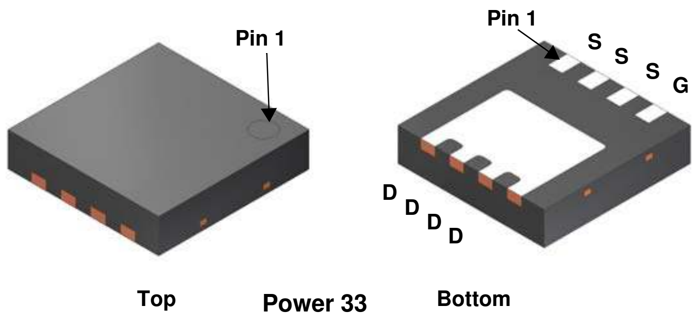
- Max $r_{DS(on)}$ = 37 mΩ at V_{GS} = 10 V, I_D = 5.5 A
- Max $r_{DS(on)}$ = 41 mΩ at V_{GS} = 6 V, I_D = 5.0 A
- Low Profile - 0.8 mm max in Power 33
- 100% UIL Tested
- RoHS Compliant

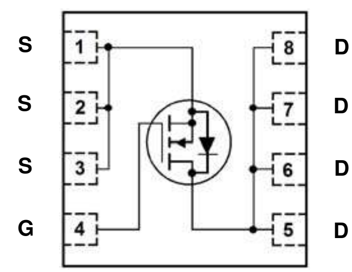
General Description

This N-Channel MOSFET is produced using ON Semiconductor's advanced PowerTrench® technology. This very high density process is especially tailored to minimize on-state resistance and optimized for hot swap application.

Applications

- DC - DC Conversion
- PSE Switch





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	-Continuous T_A = 25°C (Note 1a)	5.5	A
	-Pulsed (Note 4)	130	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	181	mJ
P_D	Power Dissipation T_C = 25°C	50	W
	Power Dissipation T_A = 25°C (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	53	

Package Marking and Ordering Information

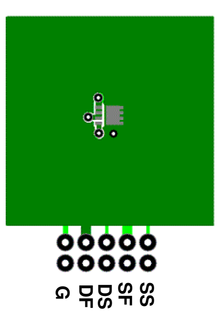
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC035N10	FDMC035N10X1	Power 33	13”	12 mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		107		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	2.5	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		-7		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 5.5 A		30	37	mΩ
		V_{GS} = 6 V, I_D = 5.0 A		32	41	
		V_{GS} = 10 V, I_D = 5.5 A, T_J = 125°C		60	75	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 5.5 A		18		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1MHz		1910	2675	pF
C_{oss}	Output Capacitance			109		pF
C_{rss}	Reverse Transfer Capacitance			64		pF
R_g	Gate Resistance		0.1	2.6	5.2	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 5.5 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		12	21	ns
t_r	Rise Time			7	13	ns
$t_{d(off)}$	Turn-Off Delay Time			56	90	ns
t_f	Fall Time			14	25	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 5.5 A		41	58	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 6 V; V_{DD} = 50 V, I_D = 5.5 A		27	38	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 50 V, I_D = 5.5 A		6.3		nC
Q_{gd}	Gate to Drain "Miller" Charge			11		nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 5.5 A (Note 2)		0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 5.5 A, di/dt = 100 A/μs		42	68	ns
Q_{rr}	Reverse Recovery Charge			58	92	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 53°C/W when mounted on a 1 in^2 pad of 2 oz copper

b) 125°C/W when mounted on a minimum pad

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.
3. E_{AS} of 181 mJ is based on starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 11 A, V_{DD} = 100 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 35 A.
4. Pulsed Id please refer to Fig 11 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics T_J = 25 °C unless otherwise noted.

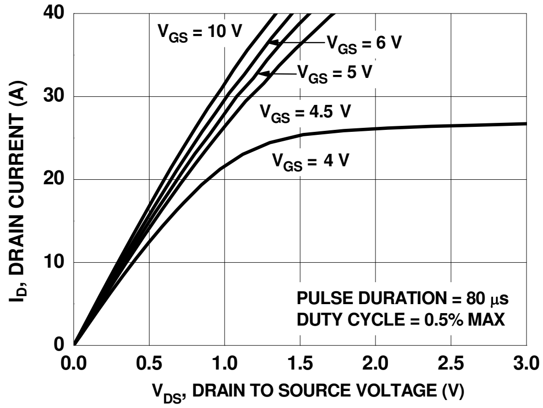


Figure 1. On Region Characteristics

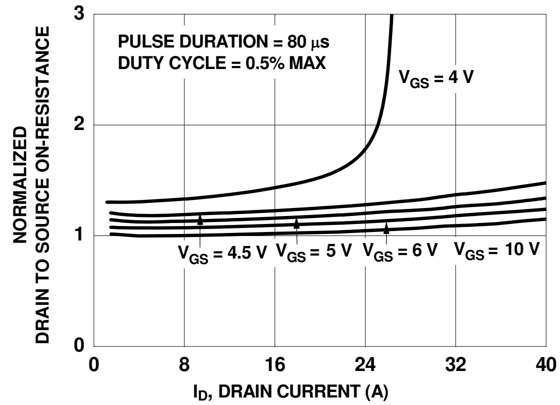


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

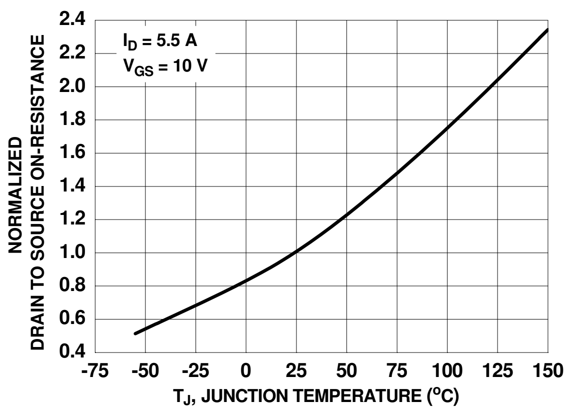


Figure 3. Normalized On Resistance vs. Junction Temperature

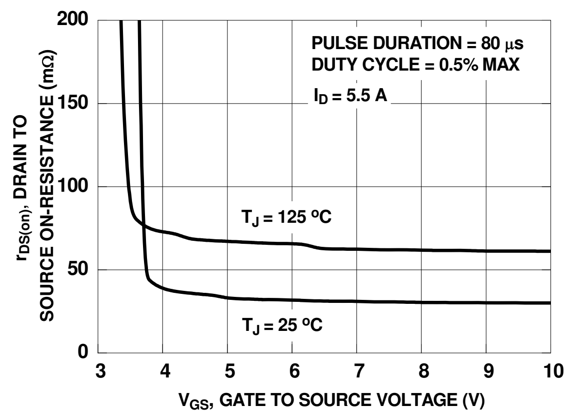


Figure 4. On-Resistance vs. Gate to Source Voltage

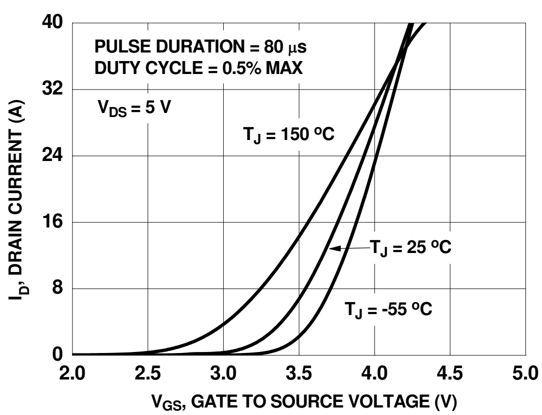


Figure 5. Transfer Characteristics

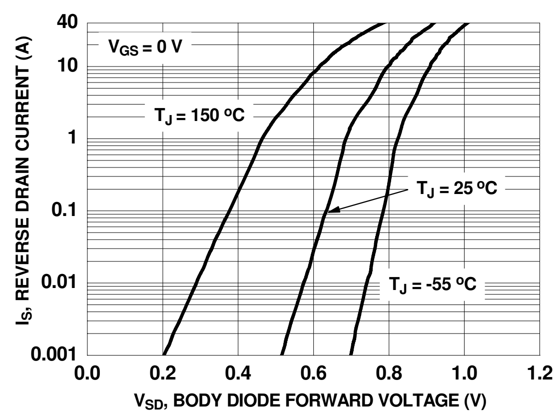


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted.

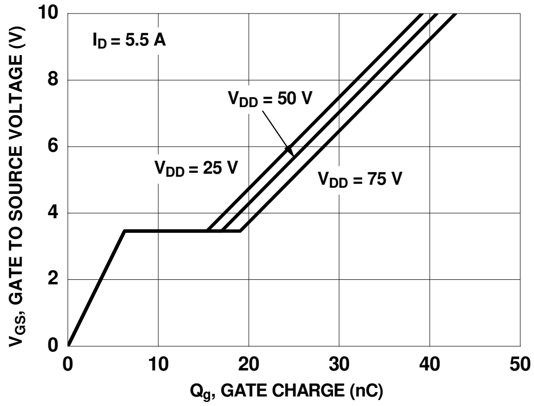


Figure 7. Gate Charge Characteristics

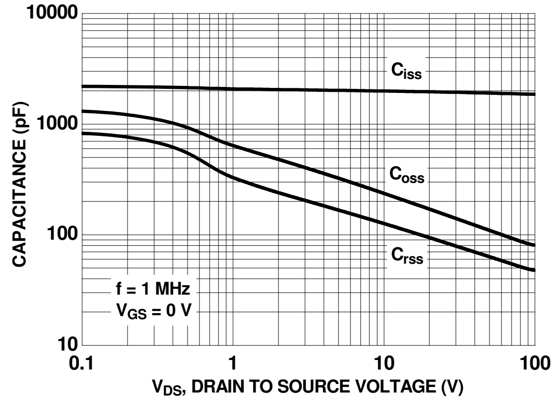


Figure 8. Capacitance vs. Drain to Source Voltage

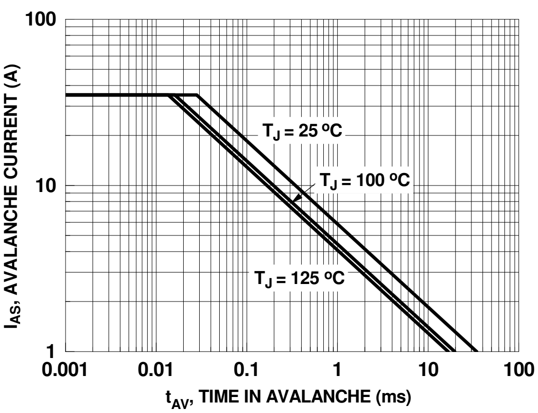


Figure 9. Unclamped Inductive Switching Capability

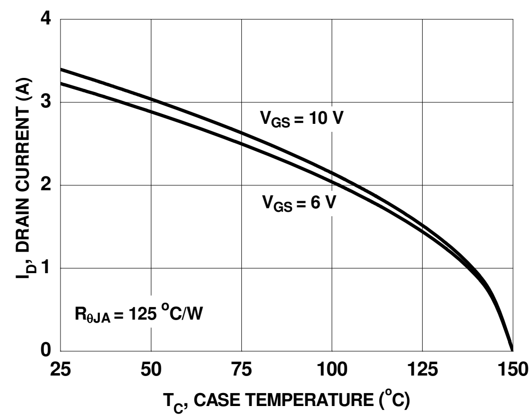


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

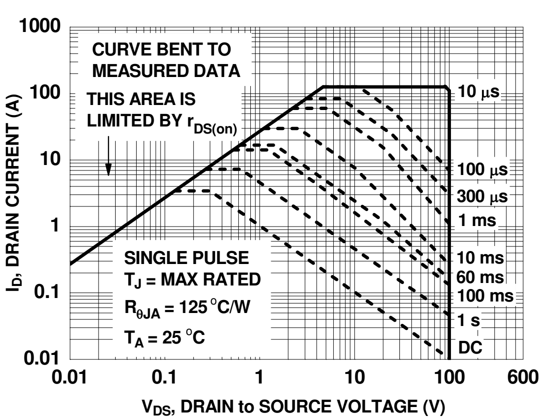


Figure 11. Forward Bias Safe Operating Area

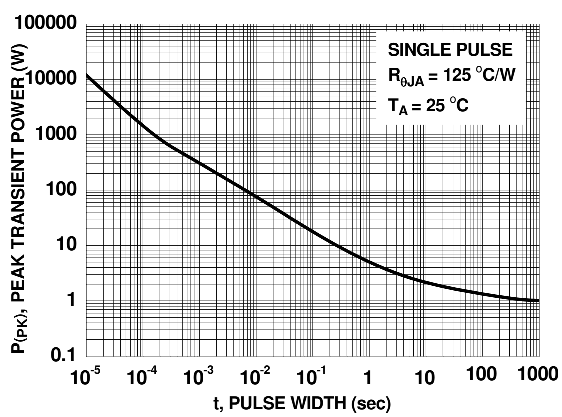


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted.

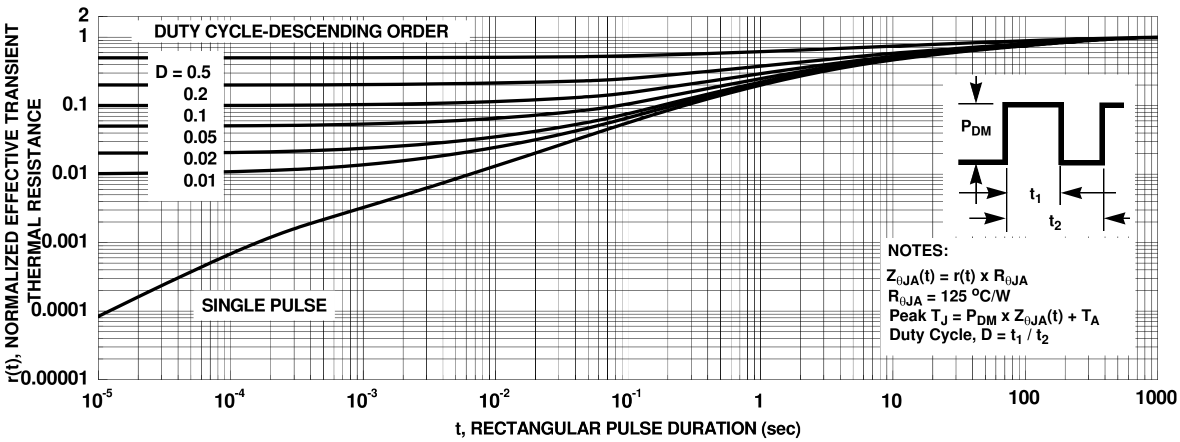
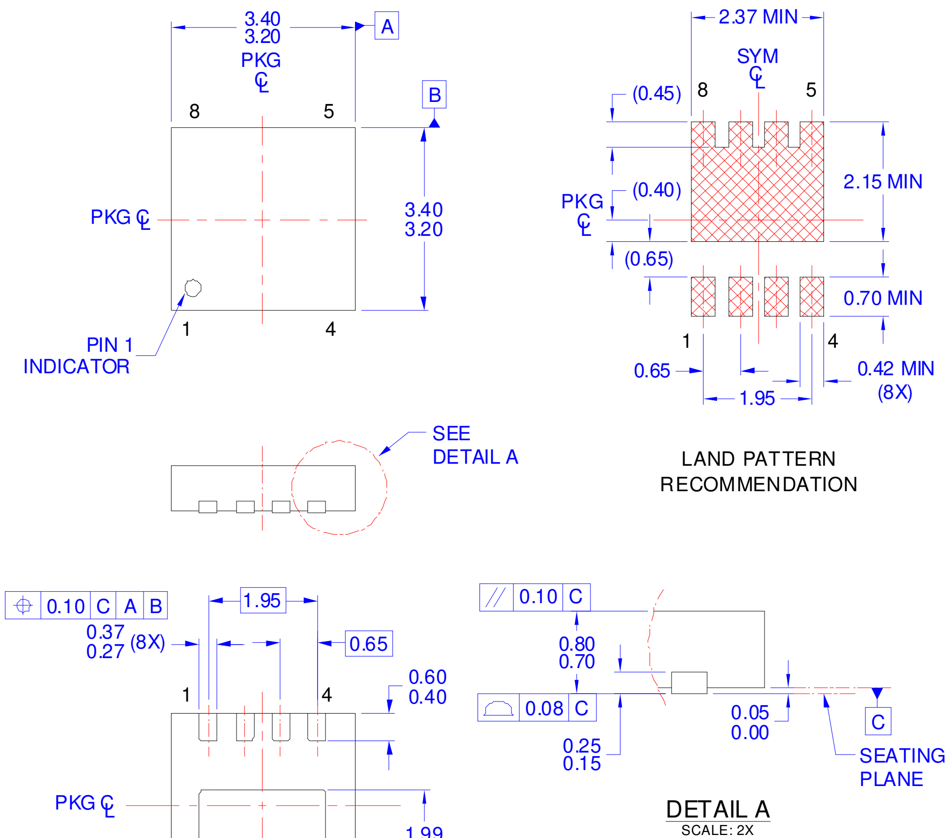


Figure 13. Junction to Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA,
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E) DRAWING FILE NAME: MKT-PQFN08SREV1

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